Ordering number : ENN7018

P-Channel Silicon MOSFET

CPH6315

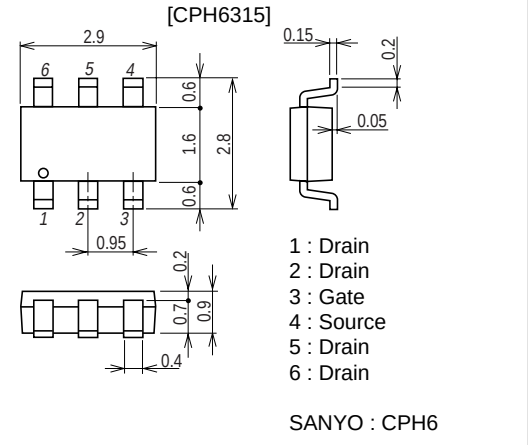
High-Speed Switching Applications

Features

- Low ON-resistance.
- High-speed switching.
- 2.5V drive.

Package Dimensions

unit : mm
2151A



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		-20	V
Gate-to-Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		-3	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	-12	A
Allowable Power Dissipation	P_D	Mounted on a ceramic board (1200mm²×0.8mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=-1mA, V_{GS}=0	-20			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=-20V, V_{GS}=0			-10	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GSS}=±8V, V_{DS}=0			±10	μA
Cutoff Voltage	$V_{GS}(off)$	V_{DS}=-10V, I_D=-1mA	-0.3		-1.4	V
Forward Transfer Admittance	$\|yfs\|$	V_{DS}=-10V, I_D=-1A	2.1	3		S
Static Drain-to-Source On-State Resistance	$R_{DS}(on)1$	I_D=-1A, V_{GS}=-4V		115	150	mΩ
	$R_{DS}(on)2$	I_D=-0.5A, V_{GS}=-2.5V		145	210	mΩ

Marking : JR

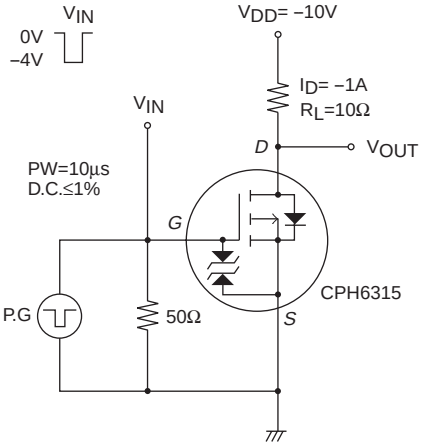
Continued on next page.

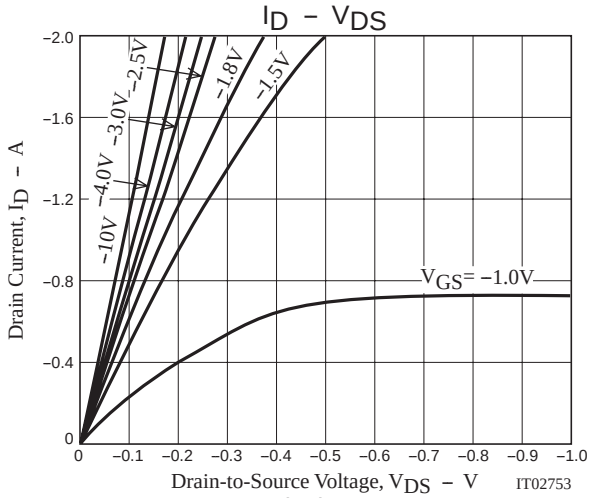
SANYO Electric Co.,Ltd. Semiconductor Company
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

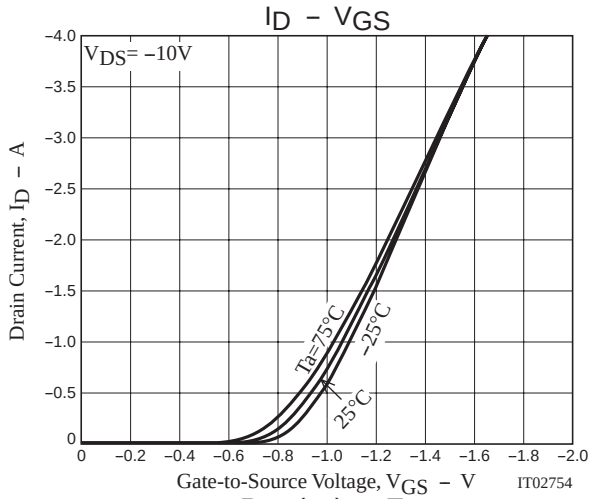
Continued from preceding page.

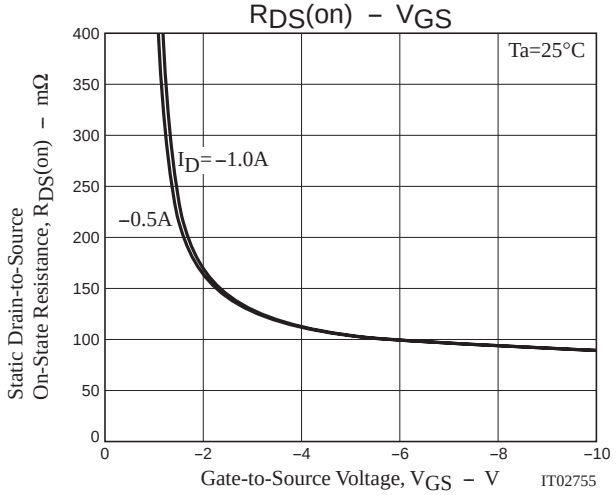
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V_{DS}=–10V, f=1MHz		410		pF
Output Capacitance	Coss	V_{DS}=–10V, f=1MHz		60		pF
Reverse Transfer Capacitance	Crss	V_{DS}=–10V, f=1MHz		40		pF
Turn-ON Delay Time	t_{d}(on)	See specified Test Circuit.		9		ns
Rise Time	t_{r}	See specified Test Circuit.		27		ns
Turn-OFF Delay Time	t_{d}(off)	See specified Test Circuit.		42		ns
Fall Time	t_{f}	See specified Test Circuit.		38		ns
Total Gate Charge	Qg	V_{DS}=–10V, V_{GS}=-4V, I_{D}=-2A		4.5		nC
Gate-to-Source Charge	Qgs	V_{DS}=–10V, V_{GS}=-4V, I_{D}=-2A		0.6		nC
Gate-to-Drain “Miller” Charge	Qgd	V_{DS}=–10V, V_{GS}=-4V, I_{D}=-2A		1.2		nC
Diode Forward Voltage	V_{SD}	I_{S}=–2A, V_{GS}=0		–0.88	–1.2	V

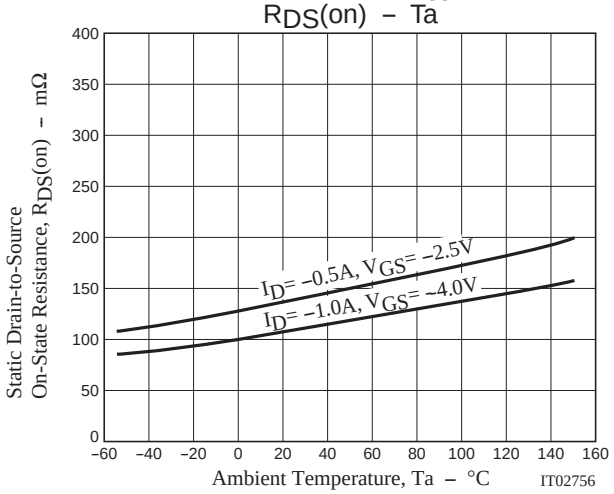
Switching Time Test Circuit

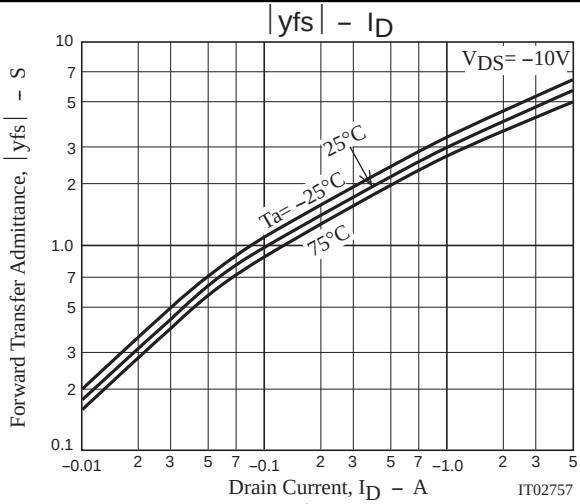


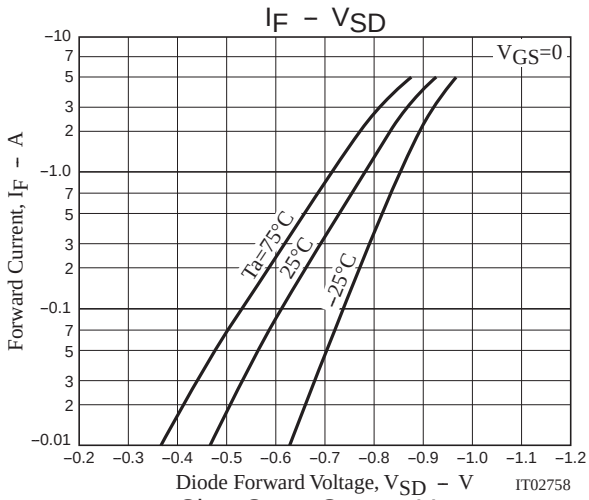


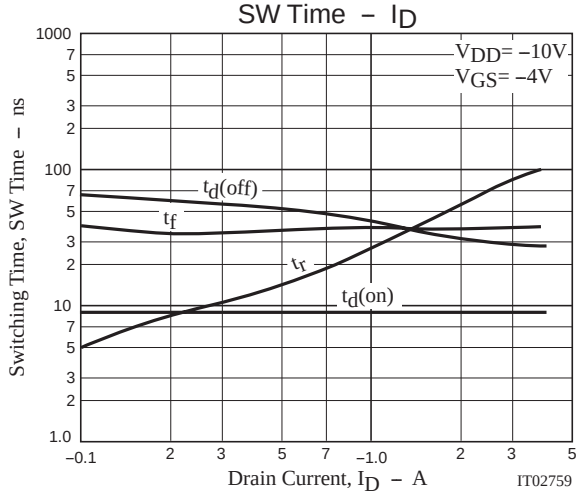


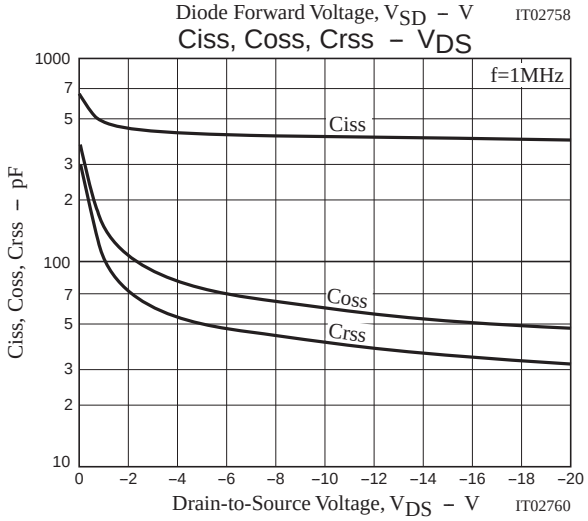


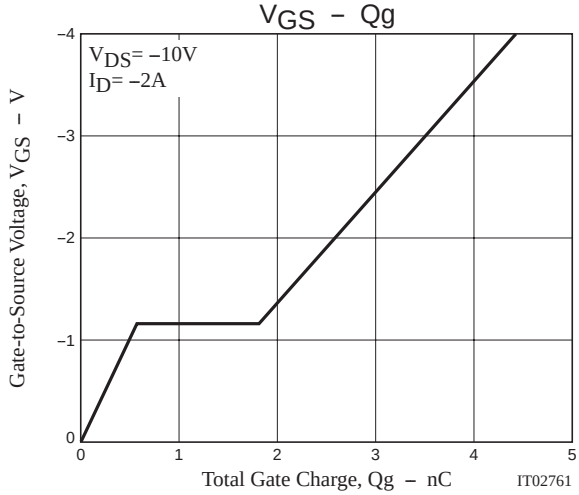


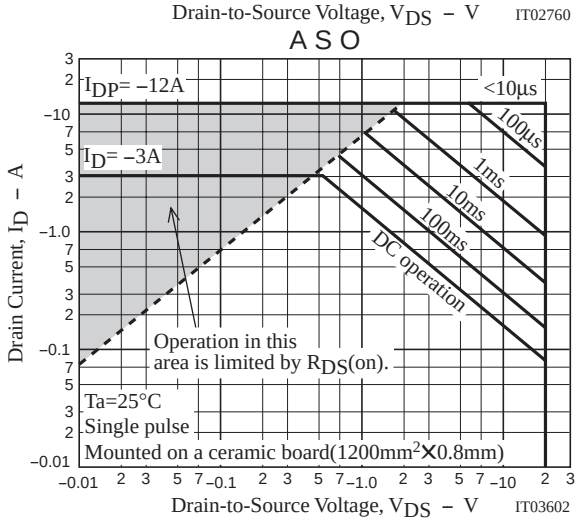

|yfs| – ID
VDS= –10V
25°C
Ta= –25°C
75°C
Forward Transfer Admittance, |yfs| – S
Drain Current, ID – A
IT02757

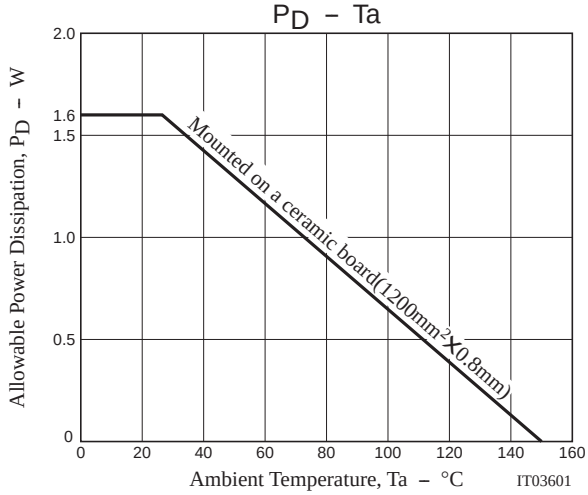

IF – VSD
VGS=0
Ta=75°C
25°C
–25°C
Forward Current, IF – A
Diode Forward Voltage, VSD – V
IT02758


SW Time – ID
VDD= –10V
VGS= –4V
td(off)
tf
tr
td(on)
Switching Time, SW Time – ns
Drain Current, ID – A
IT02759


Ciss, Coss, Crss – VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT02760


VGS – Qg
VDS= –10V
ID= –2A
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT02761


A S O
IDP= –12A
ID= –3A
<10μs
100μs
1ms
10ms
100ms
DC operation
Operation in this
area is limited by RDS(on).
Ta=25°C
Single pulse
Mounted on a ceramic board(1200mm2×0.8mm)
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT03602


PD – Ta
Mounted on a ceramic board(1200mm2×0.8mm)
Allowable Power Dissipation, PD – W
Ambient Temperature, Ta – °C
IT03601